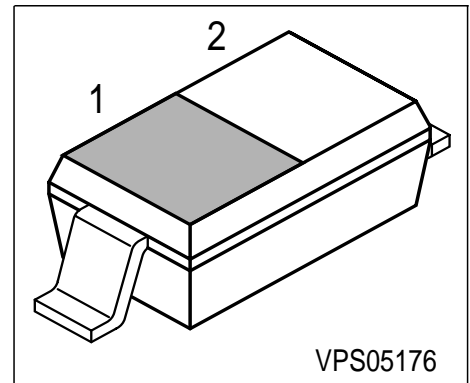


Silicon Variable Capacitance Diode

- For Hyperband TV / VTR tuners, Bd I



Type	Marking	Pin Configuration		Package
BB640	red S	1 = C	2 = A	SOD323

Maximum Ratings

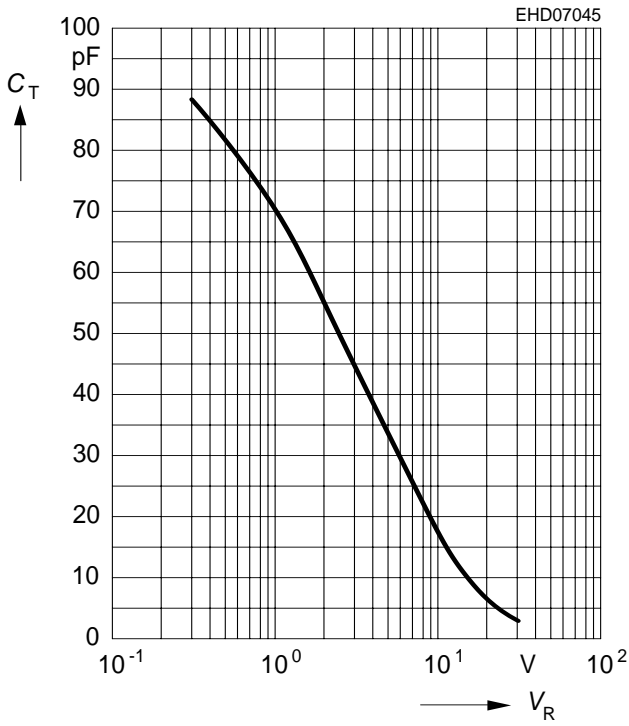
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \geq 5k\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	°C
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

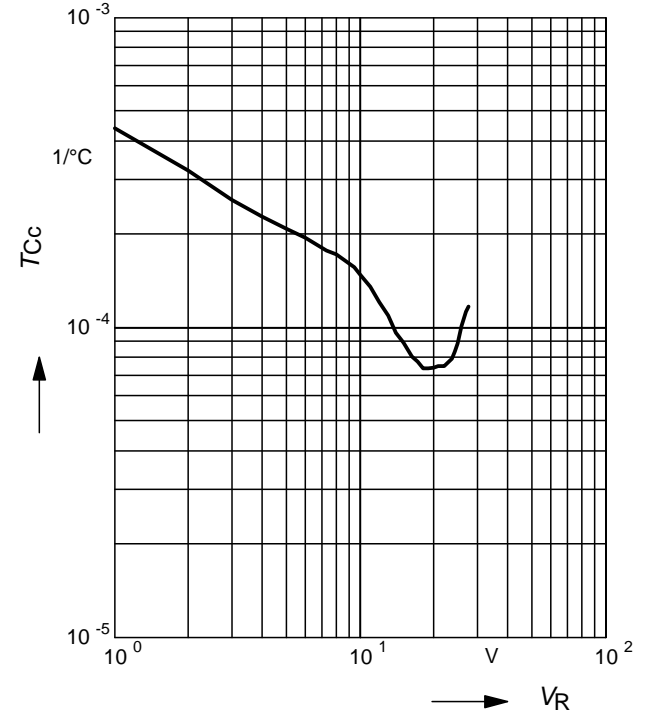
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 30\text{ V}$	I_R	-	-	10	nA
Reverse current $V_R = 30\text{ V}, T_A = 85^\circ\text{C}$	I_R	-	-	200	
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	62 47.5 2.85 2.8	69 54.5 3.28 3.05	76 61.5 3.7 3.7	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	19.5	-	25	-
Capacitance ratio $V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	C_{T2}/C_{T25}	15	16.6	-	
Capacitance matching $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	2.5	%
Series resistance $C_T = 12\text{ pF}, f = 100\text{ MHz}$	r_s	-	1.15	-	Ω
Series inductance	L_s	-	1.8	-	nH

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

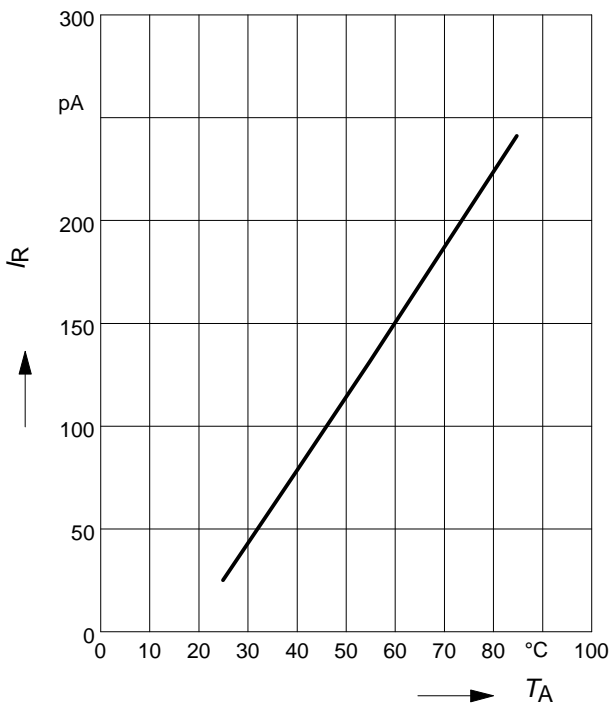


Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



Reverse current $I_R = f(T_A)$

$V_R = 28\text{V}$



Reverse current $I_R = f(V_R)$

$T_A = \text{Parameter}$

